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PATENT APPLICATION

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of

Attn: OIPE

Izumi FUSEGAWA et al.

Group Art Unit: 1722

Application No.: 10/568,186

Docket No.: 126961

Filed: February 13, 2006

For:

METHOD FOR PRODUCING A SINGLE CRYSTAL AND SILICON SINGLE

CRYSTAL WAFER

REQUEST FOR CORRECTION OF PALM RECORDS

Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

Sir:

Attached is a photocopy of the original filing receipt on which errors have been corrected in red. These errors are being brought to the attention of the Patent and Trademark Office so that it may correct its records. A Supplemental Application Data Sheet is attached.

Respectfully submitted,

William P. Berridge Registration No. 30,024

Linda M. Saltiel

Registration No. 51,122

WPB:LMS/nxy

Date: August 9, 2006

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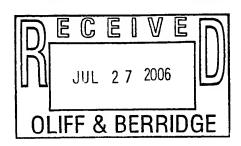


Patent and Trademark Office

UNITED STATES DEPARTMENT OF United States Patent and Trademark Office Address: COMMISSIONER FOR PATENTS P. Dex 1459 Alexandria, Viginia 22313-1450 www.uspto.gov

FILING OR 371 TOT CLMS IND CLMS DRAWINGS ART UNIT **FIL FEE REC'D** ATTY.DOCKET NO APPL NO. (c) DATE 2 126961 10/568,186 03/03/2006 1722 1030

25944 **OLIFF & BERRIDGE, PLC** P.O. BOX 19928 ALEXANDRIA, VA 22320



CONFIRMATION NO. 5592

FILING RECEIPT *OC000000019700293*

Date Mailed: 07/21/2006

Receipt is acknowledged of this regular Patent Application. It will be considered in its order and you will be notified as to the results of the examination. Be sure to provide the U.S. APPLICATION NUMBER, FILING DATE, NAME OF APPLICANT, and TITLE OF INVENTION when inquiring about this application. Fees transmitted by check or draft are subject to collection. Please verify the accuracy of the data presented on this receipt. If an error is noted on this Filing Receipt, please mail to the Commissioner for Patents P.O. Box 1450 Alexandria Va 22313-1450. Please provide a copy of this Filing Receipt with the changes noted thereon. If you received a "Notice to File Missing Parts" for this application, please submit any corrections to this Filing Receipt with your reply to the Notice. When the USPTO processes the reply to the Notice, the USPTO will generate another Filing Receipt incorporating the requested corrections (if appropriate).

Applicant(s)

Izumi Fusegawa, Fukushima, JAPAN; Nobuaki Mitamuria, Fukushima, JAPAN; Nobuaki Mitamura Takahiro Yanagimachi, Fukushima, JAPAN;

Assignment For Published Patent Application

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Power of Attorney: The patent practitioners associated with Customer Number 25944.

Domestic Priority data as claimed by applicant

This application is a 371 of PCT/JP04/11685 08/13/2004

Foreign Applications

2003-246637

JAPAN 2003296837 08/20/2003

If Required, Foreign Filing License Granted: 07/20/2006

The country code and number of your priority application, to be used for filing abroad under the Paris **Convention, is US10/568,186**

Projected Publication Date: 10/26/2006

Non-Publication Request: No

Early Publication Request: No

Title

Method for Producing a single crystal and silicon single crystal water

Process for producing single crystal and silicon crystal water

Preliminary Class

117

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Supplemental Application Data Sheet

Applicant Information

Applicant Authority type:: Inventor

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Status:: Full Capacity

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Country of Residence:: Japan

Correspondence Information

Correspondence Customer Number:: 25944

Application Information

Application Type:: National Phase

Subject Matter:: Utility CD-ROM or CD-R:: None

Title::

METHOD FOR PRODUCING A SINGLE

CRYSTAL AND SILICON SINGLE

CRYSTAL WAFER

Attorney Docket Number::

126961

Suggested Drawing Figure::

1

Total Drawing Sheets::

5

Small Entity::

No

Representative Information

Attorneys associated with Customer No. 25944.

Domestic Priority In	formation		
Application::	Continuity Type::	Parent Application::	Parent Filing Date::
			00/40/04
This Application is a	National Stage of	PCT/JP2004/011685	08/13/04
Foreign Priority Info	rmation		
Country::	Application Number::	Filing Date::	Priority Claimed::
Japan	2003-296837	08/20/03	Yes
Assignee Information	on		-
Assignee Name::		Shin-Etsu Handotai Co., Ltd.	
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